

NOT RECOMMENDED FOR NEW DESIGN USE DMN2056U



DMG2302U

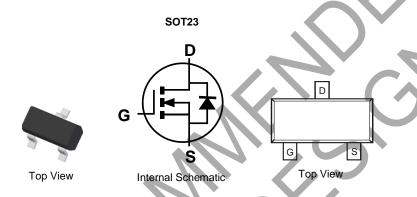
N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMG2302UQ)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



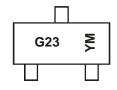
Ordering Information (Note 4)

		•
Part Number	Case	Packaging
DMG2302U-7	SOT23	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



G23 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: E = 2017) M = Month (ex: 9 = September)

Date Code Key

	Year	2009	_	2015	2016	201	17 20°	18 201	9 202	0 2021	2022	2023	2024	2025
	Code	W	_	С	D	E	·	G	Н		J	K	L	M
ſ	Month	Ja	n F	eb M	lar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Ī	Code	1		2	3	4	5	6	7	8	9	0	N	D



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Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characte	eristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 5)	$T_A = +25$ °C $T_A = +70$ °C	I _D	4.2 3.4	А	
Pulsed Drain Current (10µs Pulse, Dut	Note 6)	I _{DM}	27	Α	

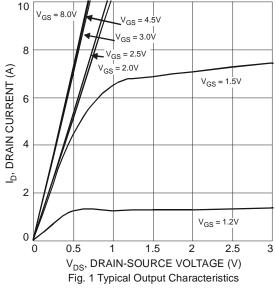
Thermal Characteristics

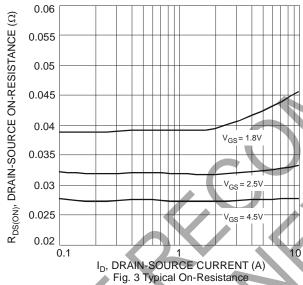
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_{D}	8.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	156	°C/W
Total Power Dissipation (Note 6)		P _D	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	91	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

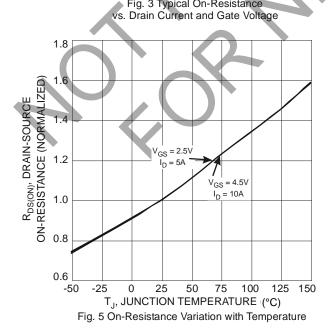
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

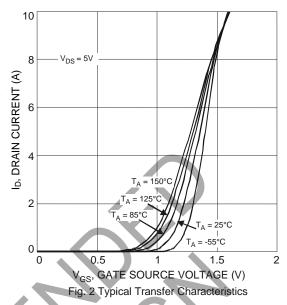
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	-		V	$V_{GS} = 0V, I_{D} = 10\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}			100	nA	$V_{DS} = 16V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}			±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.4	_	1.0	V	$V_{DS} = V_{GS}$, $I_D = 50\mu A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	_	90 120	mΩ	$V_{GS} = 4.5V, I_D = 3.6A$ $V_{GS} = 2.5V, I_D = 3.1A$
Forward Transfer Admittance	Y _{fs}		13	_	S	$V_{DS} = 5V, I_D = 3.6A$
Diode Forward Voltage	V _{SD}		0.75	1.0	V	$V_{GS} = 0V$, $I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 8)		1 1			•	
Input Capacitance	Ciss	-	594.3	_	pF	
Output Capacitance	Coss	þ	64.5	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	—	57.7	_	pF	1 = 1.0WH 12
Gate Resistance	R_{g}	_	1.5	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge	Q_{g}	_	7.0	_	nC	1, 1,5), 1, 1,0),
Gate-Source Charge	Q _{gs}	_	0.9	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$
Gate-Drain Charge	Q _{gd}	_	1.4	_	nC	$I_D = 3.6A$
Turn-On Delay Time	t _{D(ON)}	_	7.4	_	ns	
Turn-On Rise Time	t _R	_	9.8	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	_	28.1	_	ns	$R_L = 2.78\Omega$, $R_G = 1.0\Omega$
Turn-Off Fall Time	t _F	_	6.7	_	ns	<u> </u>

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. copper, single sided.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.









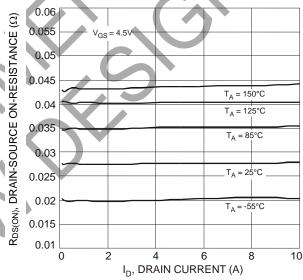
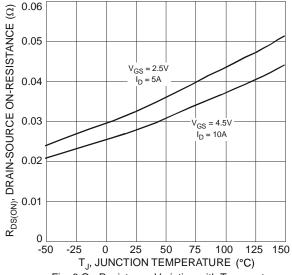


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature





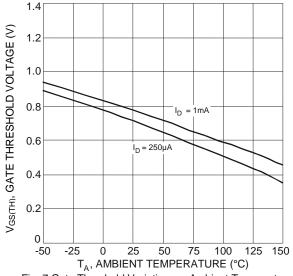
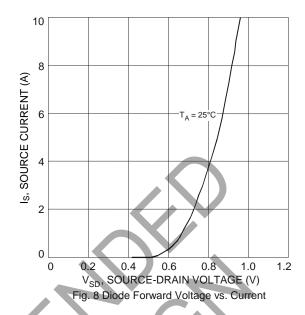
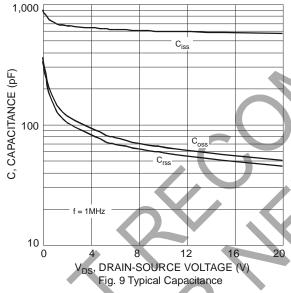
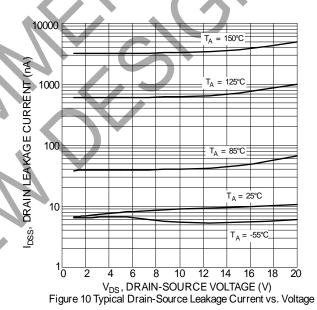


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







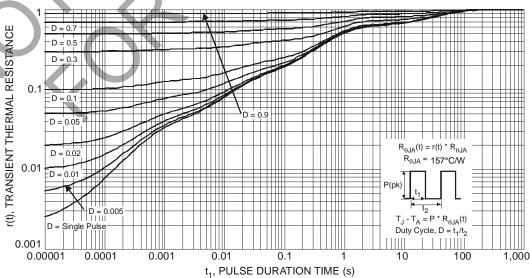


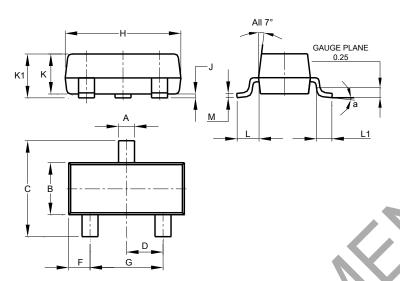
Fig. 11 Transient Thermal Response

DMG2302U

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

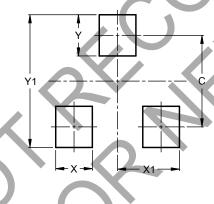


SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
U	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	29



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